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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
10/665,897	09/18/2003	Peter J. Hopper	NSC1P282/P05730	6996
22434 75	90 03/17/2005	03/17/2005		
	VER & THOMAS L	ROSE, KIESHA L		
P.O. BOX 70250 OAKLAND, CA 94612-0250			ART UNIT	PAPER NUMBER
Orneland, C	71 71072 0230		2822	

DATE MAILED: 03/17/2005

Please find below and/or attached an Office communication concerning this application or proceeding.

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	Application No.	Applicant(s)		
Office Action Commence	10/665,897	HOPPER ET AL.		
Office Action Summary	Examiner	Art Unit		
	Kiesha L. Rose	2822		
The MAILING DATE of this communication app Period for Reply	ears on the cover sheet with the c	orrespondence address		
A SHORTENED STATUTORY PERIOD FOR REPLY THE MAILING DATE OF THIS COMMUNICATION. - Extensions of time may be available under the provisions of 37 CFR 1.13 after SIX (6) MONTHS from the mailing date of this communication. - If the period for reply specified above is less than thirty (30) days, a reply If NO period for reply is specified above, the maximum statutory period who Failure to reply within the set or extended period for reply will, by statute, Any reply received by the Office later than three months after the mailing earned patent term adjustment. See 37 CFR 1.704(b).	i6(a). In no event, however, may a reply be time within the statutory minimum of thirty (30) days ill apply and will expire SIX (6) MONTHS from cause the application to become ABANDONEI	nely filed s will be considered timely. the mailing date of this communication. O (35 U.S.C. § 133).		
Status				
1) Responsive to communication(s) filed on 08 Fe	bruary 2005.			
2a) This action is FINAL . 2b) ⊠ This	action is non-final.			
3) Since this application is in condition for allowan	ce except for formal matters, pro	secution as to the merits is		
closed in accordance with the practice under E	x parte Quayle, 1935 C.D. 11, 45	3 O.G. 213.		
Disposition of Claims				
4) Claim(s) 1-25 is/are pending in the application.				
4a) Of the above claim(s) 17-25 is/are withdraw	n from consideration.			
5) Claim(s) is/are allowed.				
6)⊠ Claim(s) <u>1-16</u> is/are rejected.				
7) Claim(s) is/are objected to.				
8) Claim(s) are subject to restriction and/or	election requirement.			
Application Papers				
9) The specification is objected to by the Examine	r.			
10)☐ The drawing(s) filed on is/are: a)☐ acce	epted or b) objected to by the E	Examiner.		
Applicant may not request that any objection to the	drawing(s) be held in abeyance. See	e 37 CFR 1.85(a).		
Replacement drawing sheet(s) including the correcti	on is required if the drawing(s) is obj	ected to. See 37 CFR 1.121(d).		
11) The oath or declaration is objected to by the Ex	aminer. Note the attached Office	Action or form PTO-152.		
Priority under 35 U.S.C. § 119				
12) ☐ Acknowledgment is made of a claim for foreign a) ☐ All b) ☐ Some * c) ☐ None of:	priority under 35 U.S.C. § 119(a)	-(d) or (f).		
1. ☐ Certified copies of the priority documents have been received.				
2. Certified copies of the priority documents		on No		
3. ☐ Copies of the certified copies of the prior	• •			
application from the International Bureau	(PCT Rule 17.2(a)).	·		
* See the attached detailed Office action for a list of		d.		
·				
Attachment(s)	_			
1) Notice of References Cited (PTO-892) 2) Notice of Draftsperson's Patent Drawing Review (PTO-948)	4) 🔲 Interview Summary Paper No(s)/Mail Da			
2) \(\subseteq \text{ Notice of Draftsperson's Patent Drawing Review (P1O-948)} \) 3) \(\subseteq \text{ Information Disclosure Statement(s) (PTO-1449 or PTO/SB/08)} \)	5) 🔲 Notice of Informal P	atent Application (PTO-152)		
Paper No(s)/Mail Date 9/18/03.	6) Other:	•		

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DETAILED ACTION

This Office Action is in response to the election filed 8 February 2005.

Election/Restrictions

Claims 17-25 are withdrawn from further consideration pursuant to 37 CFR 1.142(b) as being drawn to a nonelected method of making a semiconductor device, there being no allowable generic or linking claim. Election was made **without** traverse in the reply filed on 8 February 2005.

Applicant's election without traverse of claims 1-16 in the reply filed on 8 February 2005 is acknowledged.

Claim Rejections - 35 USC § 112

The following is a quotation of the second paragraph of 35 U.S.C. 112:

The specification shall conclude with one or more claims particularly pointing out and distinctly claiming the subject matter which the applicant regards as his invention.

Claim 1 recites the limitation "active silicon layer" in claim 1. There is insufficient antecedent basis for this limitation in the claim.

Claim Rejections - 35 USC § 102

The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless -

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(e) the invention was described in (1) an application for patent, published under section 122(b), by another filed in the United States before the invention by the applicant for patent or (2) a patent granted on an application for patent by another filed in the United States before the invention by the applicant for patent, except that an international application filed under the treaty defined in section 351(a) shall have the effects for purposes of this subsection of an application filed in the United States only if the international application designated the United States and was published under Article 21(2) of such treaty in the English language.

Claims 1-7 and 9-11 are rejected under 35 U.S.C. 102(e) as being anticipated by Lin (U.S. Patent 6,483,147).

Lin discloses a silicon-on-insulator device (Fig. 8) that contains an active semiconductor layer (32), a MOS transistor (42) or other forms of transistors formed in the active silicon layer, a bulk silicon layer (12) having a first surface and second surface, an oxide layer (34) formed between the active silicon layer and first surface of the bulk silicon layer, a heat sink (38) formed in the bulk silicon layer and configured to sink heat sourced through the oxide layer to the second surface of the bulk silicon layer, where the heat sink is a thermally conductive metal material (tungsten-titanium) provided in a plug and is substantially the same size as the thickness of the bulk silicon layer and has a circumference ranging from 1 to 50000 microns and where the silicon-on-insulator is formed on a semiconductor wafer or die.

Claim Rejections - 35 USC § 103

The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:

(a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.

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Claims 8 and 15-16 are rejected under 35 U.S.C. 103(a) as being unpatentable over Lin in view of Mitani et al. (U.S. Publication 2003/0057491).

Lin discloses all the limitations except for an isolation region and the orientation of the semiconductor material. Whereas Mitani discloses a semiconductor device (Fig. 3) that contains a bulk silicon layer (1a), an oxide layer (2a), a active silicon layer (3a), a transistor and isolation regions (4) formed around the transistor and contacting the oxide layer, where the bulk silicon layer, oxide layer and active silicon layer have an orientation of 100,111 or 110). The isolation regions are formed around the transistors to act as element isolations to separate other transistors or elements from each other. Therefore it would have been obvious to one having ordinary skill in the art at the time the invention was made to modify the device of Lin by incorporating an isolation region to act as a element isolations to separate other transistors or elements from each other as taught by Mitani. In regards to the orientation, it is well known in the art to have semiconductor materials formed of orientations 110,111 or 110 as disclosed in the Mitani reference.

Claims 12-14 are rejected under 35 U.S.C. 103(a) as being unpatentable over Lin.

Lin discloses the claimed invention except for a plurality of transistors and heat sinks. It would have been obvious to one having ordinary skill in the art at the time the invention was made to have a plurality of transistors and heat sinks, since it has been held that mere duplication of the essential working parts of a device involves only routine skill in the art. (St. Regis Paper Co. v. Bemis Co., 193 USPQ 8 1977) In addition

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the Lin reference discloses that there is at least one heat sink or transistor so that discloses a plurality of transistors and heat sink. (Column 2, lines 15-16)

Conclusion

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Any inquiry concerning this communication or earlier communications from the examiner should be directed to Kiesha L. Rose whose telephone number is 571-272-1844. The examiner can normally be reached on M-F 8:30-6:00 off 2nd Mondays.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Amir Zarabian can be reached on 571-272-1852. The fax phone number for the organization where this application or proceeding is assigned is 703-872-9306.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

KLR

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